

Appl. No. 10/754,725
Amendment dated: December 20, 2006
Reply to OA of: September 21, 2006

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1(currently amended). A method for manufacturing a diffuser for a backlight module comprising:

- (a) providing a transparent substrate;
- (b) forming a first transparent photoresist layer on said transparent substrate;
- (c) spreading a plurality of masking particles on said first transparent photoresist layer;
- (d) exposing ~~and developing~~ said first transparent photoresist layer;
- (e) removing said masking particles; and
- (f) etching to develop said first transparent photoresist layer to form a first scattering array.

2(original). The method as claimed in claim 1 further comprising a step (g) forming a passivation layer on said first transparent photoresist layer.

3(original). The method as claimed in claim 1, wherein said first transparent photoresist layer having at least a photo-sensitive polymer and a photo initiator.

4(original). The method as claimed in claim 1, wherein said transparent substrate is made of acrylic, polyethylene terephthalate (PET), or polycarbonate (PC).

5 (original). The method as claimed in claim 1, wherein said first transparent

photoresist layer is a polyacrylate-based photoresist.

6(original). The method as claimed in claim 1, wherein said masking particles are made of glass, TiO₂, silica, or polystyrene.

7(original). The method as claimed in claim 1, wherein the particle size of said masking particles ranges from 100nm to 50 μ m.

8(original). The method as claimed in claim 2, wherein said passivation layer is made of polyacrylates, polycarbonate, polyethylene terephthalate (PET), or polyethylene (PE).

9(currently amended). The method as claimed in claim 1 further comprising the following steps after step (f):

(f-1) depositing a second transparent photoresist layer on said transparent substrate and said first scattering array;

(f-2) spreading a plurality of masking particles on said second transparent photoresist layer;

(f-3) ~~exposing and developing~~ said second transparent photoresist layer;

(f-4) removing said masking particles; and

(f-5) etching to develop said second transparent photoresist layer to form a second scattering array.

10(original). The method as claimed in claim 9 further comprising a step (g2) forming a passivation layer on said second transparent photoresist layer.

11(original). The method as claimed in claim 9, wherein said second transparent

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photoresist layer having at least a photo-sensitive polymer and a photo initiator.

12(original). The method as claimed in claim 9, wherein said second transparent photoresist layer is a polyacrylate-based photoresist.